

L-610MP4BT/BD

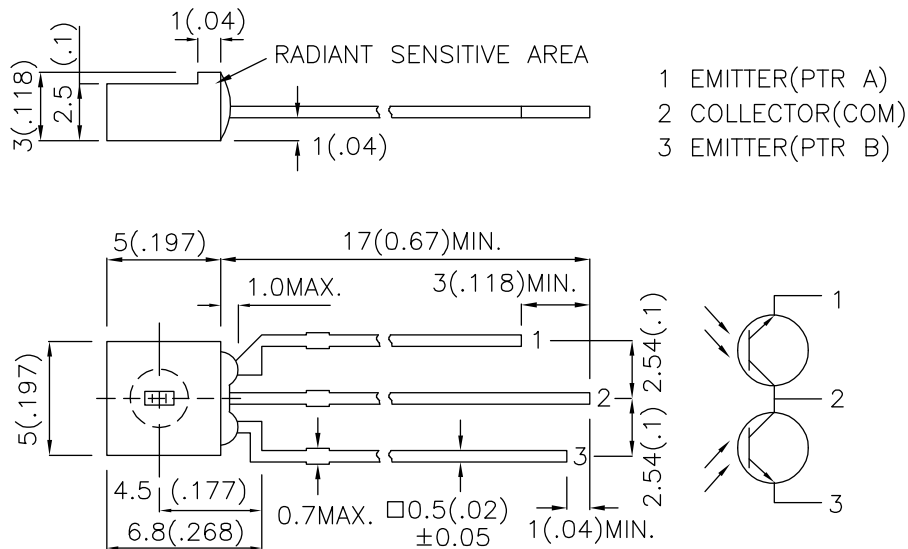
Features

- MECHANICALLY AND SPECTRALLY MATCHED TO THE KM-4457 INFRARED EMITTING LED LAMP SERIES
- BLACK DIFFUSED LENS.
- COUPLED WITH KM-4457 INFRARED EMITTING LED LAMP SERIES FOR MOUSE APPLICATION.
- RoHS COMPLIANT.

Description

Made with NPN silicon phototransistor chips.

Package Dimensions



Notes:

1. All dimensions are in millimeters (inches).
2. Tolerance is $\pm 0.25(0.01)$ " unless otherwise noted.
3. Lead spacing is measured where the leads emerge from the package.
4. Specifications are subject to change without notice.

Electrical / Optical Characteristics at T_A=25°C

Symbol	Parameter	Min.	Typ.	Max.	Units	Test Conditions
V _{BR CEO}	Collector-to-Emitter Breakdown Voltage	30	-	-	V	I _C =100uA E _e =0mW/cm ²
V _{BR ECO}	Emitter-to-Collector Breakdown Voltage	5	-	-	V	I _E =100uA E _e =0mW/cm ²
V _{CE (SAT)}	Collector-to-Emitter Saturation Voltage	-	-	0.4	V	I _C =500uA E _e =5mW/cm ²
I _{CEO}	Collector Dark Current	-	-	100	nA	V _{CE} =10V E _e =0mW/cm ²
T _R	Rise Time (10% to 90%)	-	16	-	us	V _{CE} = 5V I _C =1mA R _L =1000Ω
T _F	Fall Time (90% to 10%)	-	18	-	us	
I _(ON)	On State Collector Current	0.1	0.5	-	mA	V _{CE} = 5V E _e =1mW/cm ² λ=940nm
R	Collector Current Ratio of Phototransistor	0.8	1	1.25	Ω	I _C (on) (a)/ I _C (on) (b)

Absolute Maximum Ratings at T_A=25°C

Parameter	Max.Ratings
Collector-to-Emitter Breakdown Voltage	30V
Emitter-to-Collector Breakdown Voltage	5V
Power Dissipation at (or below) 25°C Free Air Temperature	100mW
Operating Temperature Range	-55°C ~ +100°C
Storage Temperature Range	-55°C ~ +100°C
Lead Solder Temperature (>5mm for 5sec)	260°C